Please amend the application as follows:

## IN THE CLAIMS:

Please amend claim 13 as follows:

Claim 13 (Amended). A method of CMP comprising: forming a CMP slurry having a high structure polishing rate

lower than a blanket polishing rate:

adding a slurry modifier to the slurry to produce a modified slurry that polishes high structures at a rate approximating the [blank] blanket polishing rate; and

polishing high structure areas.

Please add claims 17 through 20 as follows:

Claim 17 (New). A method of CMP comprising:

forming a CMP slurry having a low-density high structure polishing rate and a high-density high structure polishing rate, wherein the low-density high structure polishing rate is essentially the same as a high-density high structure polishing rate; and

polishing high structure areas, whereby the polishing rate is independent of pattern density.

Claim 18 (New). The method of claim 17, wherein said forming includes setting a cerium oxide concentration of between about 1% and 50% by weight.

Claim 19 (New). The method of claim 17, wherein said polishing includes CMP at a pressure of between about five psi and ten psi.

## Attachment to Preliminary Amendment Accompanying Continued Prosecution Application Under 37 § 1.53(d) Dated May 2, 2001

## Claims Pending in Application Serial No. 09/270,606 Incorporating All Changes as of May 2, 2001

1. A method of CMP comprising:

forming a CMP slurry containing cerium oxide;

adding a slurry modifier to the slurry, wherein the slurry modifier polishes low structure areas at a substantially zero rate and polishes high structure areas at a rate approximating a blanket polishing rate; and

polishing a structure using the modifier-contained

slurry.

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- 2. The method of claim 1 wherein said forming includes setting a cerium oxide concentration of between about 1% and 50% by weight.
- 3. The method of claim 1 wherein said polishing includes CMP at a pressure of between about five psi and ten psi.
- 4. The method of claim 1 wherein said adding includes adding ethylene glycol at a concentration of up to 50%.

5. A method of CMP comprising:

forming a CMP slurry containing cerium oxide at a concentration of between about 1% and 50% by weight;

adding a slurry modifier to the slurry, wherein the slurry modifier polishes low structure areas at a substantially zero rate and polishes high structure areas at a rate approximating a blanket polishing rate; and

polishing a structure using the modifier-contained

- 6. The method of claim 5 wherein said polishing includes CMP at a pressure of between about five psi and ten psi.
- 7. The method of claim 5 wherein said adding includes adding ethylene glycol at a concentration of up to 50%.
  - 8. A method of CMP comprising:

forming a CMP slurry containing cerium oxide at a concentration of between about 1% and 50% by weight;

adding ethylene glycol at a concentration of up to 50% for polishing low structure areas at a substantially zero rate and polishing high structure areas at a rate approximating a blanket polishing rate; and polishing a structure using the slurry.

9. The method of claim 8 wherein said polishing includes CMP at a pressure of between about five psi and ten psi.

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slurry.

10. A method of CMP comprising:

forming a CMP slurry containing cerium oxide;

adding a slurry modifier to the slurry to produce a modified slurry that polishes low structure areas at a substantially zero rate and polishes high structure areas at a rate approximating a blanket polishing rate; and

polishing a structure having high structure areas and low structure areas using the modified slurry, whereby high structure areas are polished at a rate approximating a blanket polishing rate and low structure areas are polished at a substantially zero rate.

- 11. The method of claim 10, wherein the high structure areas and the low structure areas are both formed of silicon dioxide.
- 12. The method of claim 10, wherein the slurry modifier is ethylene glycol.

## 13 (Amended). A method of CMP comprising:

forming a CMP slurry having a high structure polishing rate lower than a blanket polishing rate;

adding a slurry modifier to the slurry to produce a modified slurry that polishes high structures at a rate approximating the blanket polishing rate; and

polishing high structure areas.

14. The method of claim 13, wherein the CMP slurry comprises cerium oxide.

- 15. The method of claim 13, wherein the slurry modifier is ethylene glycol.
- 16. A method of chemically-mechanically polishing a silicon dioxide layer having high structure areas and low structure areas overlying a semiconductor substrate comprising:

forming a slurry comprising cerium oxide and ethylene glycol; and

polishing the silicon dioxide layer such that the high structure areas are polished at a rate approximating a blanket polishing rate, and the low structure areas are polished at a substantially zero rate.

Claim 17 (New). A method of CMP comprising:

forming a CMP slurry having a low-density high structure polishing rate and a high-density high structure polishing rate, wherein the low-density high structure polishing rate is essentially the same as a high-density high structure polishing rate; and

polishing high structure areas, whereby the polishing rate is independent of pattern density.

Claim 18 (New). The method of claim 17, wherein said forming includes setting a cerium oxide concentration of between about 1% and 50% by weight.

Claim 19 (New). The method of claim 17, wherein said polishing includes CMP at a pressure of between about five psi and ten psi.

Claim 20 (New). The method of claim 17, wherein said forming includes adding ethylene glycol at a concentration of up to 50%.